

# 2.5V Drive Nch+Nch MOSFET

## US6K1

### Structure

Silicon N-channel MOSFET

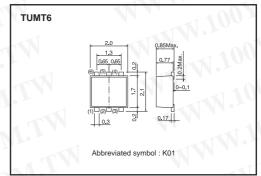
### Features

- 1) Low On-resistance.
- 2) Space savingsmall surface mount package (TUMT6).
- 3) Low voltage drive (2.5V drive).

### Applications

Switching

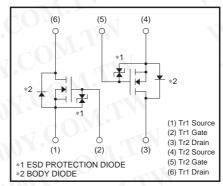
# ●Dimensions (Unit : mm)



## Packaging specifications

Mr	Package	Taping		
Туре	Code	TR		
	Basic ordering unit (pieces)	3000		
US6K1		0		

# ●Inner circuit



# ●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol Limits		Unit	
Drain-source voltage	V <sub>DSS</sub>	30			
Gate-source voltage		V <sub>GSS</sub>	12	V	
	Continuous	I <sub>D</sub>	±1.5	Α	
Drain current	Pulsed	IDP *1	±6	Α	
Source current	Continuous	Is	0.6	A	
(Body diode)	Pulsed	I <sub>SP</sub> *1	6	Α	
Total power dissipation		Pp *2	1.0	W / TOTAL	
Total power dissipation		PU	0.7	W / ELEMENT	
Channel temperature	Tch	150	°C		
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board 勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W / TOTAL
Charmer to ambient	Kill(Cli-a)	179	°C/W / ELEMENT

<sup>\*</sup> Mounted on a ceramic board

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	4	77.	10	μΑ	V <sub>GS</sub> =12V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	30	_		V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS		7	. 1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5	Dr.	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Out in Indian			170	240	$m\Omega$	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.5V
Static drain-source on-state resistance	R <sub>DS</sub> (on)*	- <del>-</del> (	180	250	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.0V
resistance	. 00	-	240	340	$m\Omega$	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub> *	1.5	<del>-</del> C		S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.5A
Input capacitance	Ciss	47	80	_	pF	Vps= 10V
Output capacitance	Coss	Mr 7	13	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	12	(T)	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	$\sim$	7	_	ns	VDD≒ 15V
Rise time	tr *	In	9	$\sim$	ns	Ib= 0.75A
Turn-off delay time	t <sub>d (off)</sub> *	-	15		ns	V <sub>G</sub> s= 4.5V R <sub>L</sub> = 20Ω
Fall time	t <sub>f</sub> *	1-0	6		ns	$R_G = 10\Omega$
Total gate charge	Q <sub>g</sub> *	• =	1.6	2.2	nC	V <sub>DD</sub> ≒15V
Gate-source charge	Qgs *	.,-4	0.5	- • -	nC	Vgs= 4.5V
Gate-drain charge	Q <sub>gd</sub> *	1-7	0.3	- (	nC	I <sub>D</sub> = 1.5A

<sup>\*</sup>Pulsed

### ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	4	11.	1.2	V	Is= 0.6A, V <sub>GS</sub> =0V

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#### •Electrical characteristics curves

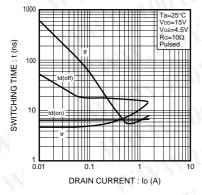


Fig.1 Switching Characteristics

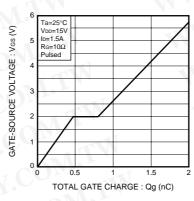


Fig.2 Dynamic Input Characteristics

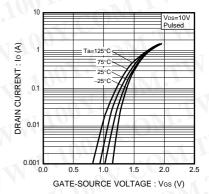


Fig.3 Typical Transfer Characteristics

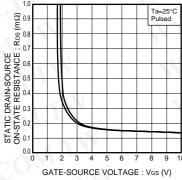


Fig.4 Static Drain-Source On-State Resistance vs. Gate source Voltage

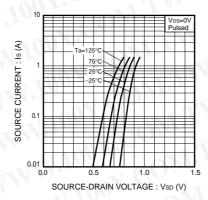


Fig.5 Source Current vs. Source-Drain Voltage

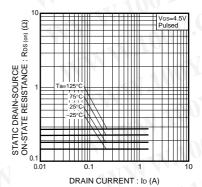


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current ( I )

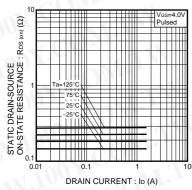


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current ( II )

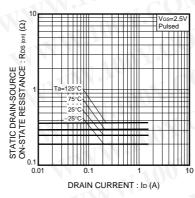


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current ( III )

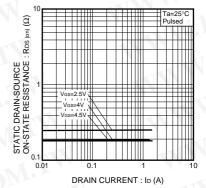


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current ( IV)

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